
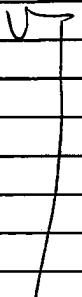

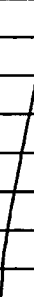


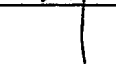
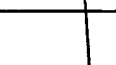
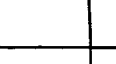

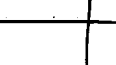
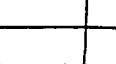
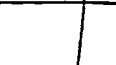
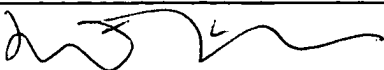

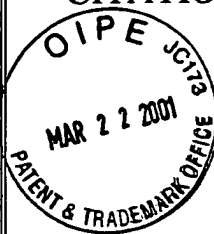
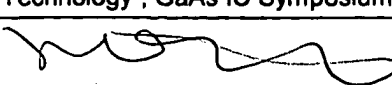


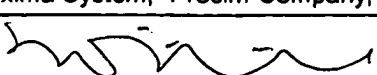


INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 50275-0014		SERIAL NO., 09/675,197	
				APPLICANT Christophe Pierrat, et al.			
				FILING DATE September 29, 2000		GROUP 2842 2823	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	4,812,962	03/14/89	Witt				
	5,051,598	09/24/91	Ashton, et al.				
	5,182,718	01/26/93	Harafugi, et al.				
	5,241,185	08/31/93	Meiri, et al.				
	5,242,770	09/07/93	Chen, et al.				
	5,256,505	10/26/93	Chen, et al.				
	5,316,878	05/31/94	Saito, et al.				
	5,326,659	07/05/94	Liu, et al.				
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
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	WO 00/67074	11/09/00	PCT				
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
	Barouch, E., et al., "OPTIMASK: An OPC Algorithm for Chrome and Phase-Shift Mask Design", 2/22-24/95, SPIE Vol. 2440, pp. 192-206.						
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

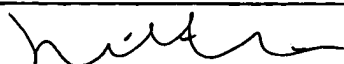
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				APPLICANT Christophe Pierrat, et al.			
				FILING DATE September 29, 2000		GROUP 2812 2825	
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W	5,340,700	08/23/94	Chen, et al.				
	5,424,154	06/13/95	Borodovsky				
	5,432,714	07/11/95	Chung, et al.				
	5,447,810	09/05/95	Chen, et al.				
	5,533,148	06/02/96	Sayah, et al.				
	5,538,815	07/23/96	Oi, et al.				
	5,553,273	09/03/96	Liebmann				
	5,572,598	11/05/96	Wihl, et al.				
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W	Henke, W., et al., "A Study of Reticle Defects Imaged Into Three-Dimensional Developed Profiles of Positive Photoresist Using the SOLID Lithography Simulator", Microelectronic Engineering 14 (1991) 283-297.						
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W	5,631,110	05/20/97	Shioiri, et al.				
	5,657,235	08/12/97	Liebmann, et al.				
	5,663,893	09/02/97	Wampler, et al.				
	5,702,848	12/30/97	Spence				
	5,705,301	01/06/98	Garza, et al.				
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	5,740,068	04/14/98	Liebmann, et al.				
	5,795,688	08/18/98	Burdorf, et al.				
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
W	Lithas: Optical Proximity Correction Software						
	MicroUnity: OPC Technology & Product Description, pp. 1-5.						
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	"Proxima System," Precim Company, Portland, Oregon (2 pages).						
EXAMINER 				DATE CONSIDERED 3/20/01			

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				APPLICANT Christophe Pierrat, et al.			
				FILING DATE September 29, 2000		GROUP 2842 2825	
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	5,801,954	09/01/98	Le, et al.				
	5,804,340	09/08/98	Garza, et al.				
	5,815,685	09/29/98	Kamon				
	5,825,647	10/20/98	Tsudaka				
	5,827,623	10/27/98	Ishida, et al.				
	5,847,959	12/08/98	Veneklasen, et al.				
	5,849,440	12/15/98	Lucas, et al.				
	5,863,682	01/26/99	Abe, et al.				
	6,081,658	06/27/00	Rieger, et al.				
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	"Proxima Wafer Proximity Correction System", Precim Company, Portland, Oregon (2 pages).						
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EXAMINER 				DATE CONSIDERED 3/2001			

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)				ATTY. DOCKET NO. 50275-0014		SERIAL NO., 09/675,197	
APPLICANT Christophe Pierrat, et al.							
FILING DATE September 29, 2000						GROUP 2812 2825	
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m	Stirniman, J., et al., "Optimizing Proximity Correction for Wafer Fabrication Processes", SPIE Vol. 2322, Photomask Technology and Management (1994), pp. 239-246.						
f	Stirniman, J., et al., "Spatial Filter Models to Describe IC Lithographic Behavior", Precim Corporation, Portland, Oregon.						
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EXAMINER 				DATE CONSIDERED 5/20/01			


EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant

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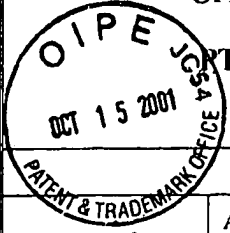


SHEET 1 OF 4

INFORMATION DISCLOSURE CITATION PTO-1449			ATTY. DOCKET NO. NTI-019-2		SERIAL NO. 09/675,197	
			APPLICANT Pierrat, et al.			
			FILING DATE 9/29/00		GROUP 2812 2825	
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W	4,231,811	11/4/80	Somekh, et al.	148	1.5	9/13/79
	4,456,371	6/26/84	Lin	355	71	6/30/82
	4,902,899	2/20/90	Lin, et al.	250	492.1	6/1/87
	5,498,579	3/12/96	Borodovsky, et al.	437	250	6/8/94
	5,553,274	9/3/96	Liebmann	395	500	6/6/95
	5,636,002	6/3/97	Garofalo	355	53	10/31/95
	5,663,017	9/2/97	Schinella, et al.	430	5	6/7/95
	5,663,893	9/2/97	Wampler et al.	364	491	5/3/95
	5,723,233	3/3/98	Garza, et al.	430	5	2/27/96
	5,766,806	6/16/98	Spence	430	5	9/9/96
	5,821,014	10/13/98	Chen, et al.	430	5	2/28/97
	5,862,058	1/19/99	Samuels, et al.	364	491	5/16/96
	5,879,844	3/9/99	Yamamoto, et al.	430	30	12/20/96
	5,885,734	3/23/99	Pierrat, et al.	430	5	8/15/96
	5,900,338	5/4/99	Garza, et al.	430	5	8/15/97
	5,994,002	11/30/99	Matsuoka	430	5	9/4/97
	6,004,702	12/21/99	Lin	430	5	5/21/98
	6,077,310	6/20/00	Yamamoto, et al.	716	19	1/29/99
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

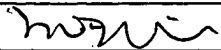
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			APPLICANT Pierrat, et al.				
			FILING DATE 9/29/00		GROUP 2812 2825		
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INFORMATION DISCLOSURE CITATION 	ATTY. DOCKET NO. NTI-019-2	SERIAL NO. 09/675,197
	APPLICANT Pierrat, et al.	
	FILING DATE 9/29/00	GROUP 282 2825
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
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	APPLICANT Pierrat, et al.	
	FILING DATE 9/29/00	GROUP 2842 2825
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PTO-1449

Atty. Docket No.

NTI-019-2

Serial No.

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

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	NTI-019-2	09/675,197
	Applicant	
	PIERRAT, Christophe	
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	9/29/2000	2825 2812

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
W	3-80525	4/5/1991	JP - ABSTRACT	X	X	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
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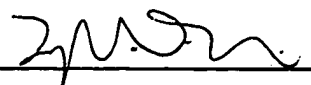
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	Applicant PIERRAT, Christophe	RECEIVED AUG. 9 2002 TECHNOLOGY CENTER 2800	
	Filing Date 9/29/2000		Group 2825 2812

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<u>m</u>	6,243.855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998

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SHEET 2 of 2

INFORMATION DISCLOSURE CITATION PTO-1449		Atty. Docket No. NTI-019-2	Serial No. 09/675,197
		Applicant PIERRAT, Christophe	Group <u>2825</u> 2811
		Filing Date 9/29/2000	
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**INFORMATION DISCLOSURE
CITATION****PTO-1449****Atty. Docket No.**

NTI-019-2

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Filing Date

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SHEET 1 of 2

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		Applicant PIERRAT, Christophe	
		Filing Date 9/29/2000	Group 2825
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